

crystallizing said semiconductor film by a first heating;  
forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and  
reducing said crystallization promoting material existing within said semiconductor island by a second heating,  
wherein irradiation of laser light is performed after forming said semiconductor film.

*[Signature]*  
25. (Amended) A method according to claim 22, wherein said crystallization promoting material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.